

Features

- Low Forward Voltage (V_F) Drop with Positive Temperature Coefficient
- Zero Reverse Recovery Current / Forward Recovery Voltage
- Temperature-Independent Switching Behavior

Applications

- Battery Chargers
- Solar & Renewable Energy Power Conversion
- Industrial Power Supplies
- Boost Diodes in PFC & DC-DC





TO247-2L Package



Part Number	Package	Qty(PCS)
HFFSH30120A	TO247-2L	30

Maximum Ratings($T = 25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Value	Unit	Test Conditions	Note	
Repetitive Peak Reverse Volta	g⊌r _{RRM}	1200	V			
DC Blocking Voltage	V _{DC}	1200	V			
Continuous Forward Current	I _F	94	A	T _J = 25 °C		
		45		T _J = 135 °C	Fig. 3	
		30		T _J = 155 °C		
Repetitive Peak Forward	I _{FRM}	121		T _c = 25 °C, t _p = 10 ms, Half Sine Pulse		
Surge Current		68		T _c = 110 °C, t _p = 10 ms, Half Sine Pulse		
Non-Repetitive Forward	I _{FSM}	233		T _c = 25 °C, t _p = 10 ms, Half Sine Pulse		
Surge Current		209		T _c = 110 °C, t _p = 10 ms, Half Sine Pulse		
Power Dissipation	P _{tot}	441	W	T _c = 25 °C	Fig. 4	
		191		T _c = 110 °C		
i²t Value	∫ i²t	271	A ² s	T _c = 25 °C, t _p = 10 ms		
		218		T _c = 110 °C, t _p = 10 ms		



Electrical Characteristics

Parameter	Symbol	Тур.	Max.	Units	Test Conditions	Note	
Forward Voltage	V _F	1.5	1.8	V	I _F = 30 A, T _J = 25 °C	Fig. 1	
		2.2	3		I _F = 30 A, T _J = 175 °C		
Reverse Current	I _R	40	250	μA	V _R = 1200 V, T _J = 25 °C	Fig. 2	
		70	450		V _R = 1200 V, T _J = 175 °C		
Total Capacitive Charge	Q _c	152		nC	V _R = 800 V, T _J = 25 °C	Fig. 5	
	с	2,177			V _R = 0 V, T _J = 25 °C, f = 1 MHz	Fig. 6	
Total Capacitance		136		pF	V _R = 400 V, T _J = 25 °C, f = 1 MHz		
		100			V _R = 800 V, T _J = 25 °C, f = 1 MHz		
Capacitance Stored Energy	E _c	44		μJ	V _R = 800 V	Fig. 7	

Note:

SiC Schottky Diodes are majority carrier devices, so there is no reverse recovery charge.

Thermal & Mechanical Characteristics

Parameter	Symbol	Value	Units	Note
Thermal Resistance, Junction to Case (Typ.)	R _{e, JC}	0.34	°C / W	
Operating Junction & Storage Temperature	T _J , T _{stg}	-55 to +175	°C	Fig. 8
Maximum Processing Temperature	T _{PROC}	325		10 min. Maximum

Electrostatic Discharge (ESD) Classifications

Parameter	Symbol	Value
Human Body Model	НВМ	Class 3B (≥ 8000 V)
Charge Device Model	СDМ	Class C3 (≥ 1000 V)



Typical Performance

T, = -55*0 T_j = 25°C T_j = 75*C 70 T_j = 125* , I₅ (A) T, = 175*C l Current, Foward 20 10 2.5 3.5 4.0 4.5 0.0 0.5 1.0 1.5 2.0 3.0 5.0 Fo rd Voltage, V_F (V)

Figure 1. Forward Characteristics

Figure 3. Current Derating



Figure 5. Total Capacitance Charge vs. Reverse Voltage



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Figure 2. Reverse Characteristics



Figure 4. Power Derating









Typical Performance

Figure 7. Capacitance Stored Energy



Figure 8. Transient Thermal Impedance



Package Dimensions

Package: TO247-2L All dimensions in mm.



	MILLIM	ETERS	INC	HES
SYM	MIN	MAX	MIN	MAX
A	4.83	5.21	.190	.205
A1	2.29	2.54	.090	.100
A2	1.91	2.16	.075	.085
b'	1.07	1.28	.042	.050
b	1.07	1.33	.042	.052
b1	1.91	2.41	.075	.095
b2	1.91	2.16	.075	.085
C'	0.55	0.65	.022	.026
С	0.55	0.68	.022	.027
D	20.80	21.10	.819	.831
D1	16.25	17.35	.640	.683
D2	2.86	3.16	.112	.124
E	15.75	16.13	.620	.635
E1	13.10	14.15	.516	.557
E2	3.68	5.10	.145	.201
E3	1.00	1.90	.039	.075
E4	12.38	13.43	.487	.529
е	10.88 B	SC	.428	BSC
L	19.81	20.32	.780	.800
L1	4.10	4.40	.161	.173
¢Ρ	3.51	3.65	.138	.144
Q	5.49	6.00	.216	.236
S	6.04	6.30	.238	.248
T		17.5° F	REF.	
W		3.5° R	EF.	
X		4° REF		
Y	0	0.50	0	0.020

Recommended Solder Pad Layout



all units are in inches



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